

Control of dispersion frequency of BaTiO₃-based ceramics applicable to thin absorber for millimeter electromagnetic wave

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Available online 22 November 2005

Abstract

Elements such as B, Li and Na were doped to barium titanate, BaTiO₃ in order to control dielectric dispersion. Addition of 3 mol% Li₂O lowered the dispersion at frequency of 0.53 MHz, while addition of 3 mol% B₂O₃ or Na₂O did not affect dispersion frequency. BaTiO₃ doped with 0.3 mol% Li₂O showed dielectric dispersion at around 2.5 GHz. An electromagnetic (EM) wave absorber using the doped BaTiO₃ plate was tried to produce for millimeter frequency range. A matching layer of 0.5 mm thick ceramic plate with relative permittivity 21 was attached to it to suppress reflection of incident EM wave due to the discontinuity at the boundary between the BaTiO₃ and air. The obtained EM wave absorber had reflectivity of –45 dB at 31 GHz and –25 dB at 95 GHz, respectively.

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Keywords: Ferroelectrics; BaTiO₃ and titanates; Dielectric properties; Powder-solid state reactions; Electromagnetic wave absorber

1. Introduction

In order to perform testing of antennas or radar systems in anechoic rooms, the electromagnetic (EM) wave absorber were developed for the first time, which were composed of a pyramidal shaped foamed plastics dispersed with carbon powder.^{1,2} Further, the ferrite EM wave absorber was newly developed for shutting out ghost images on the television display by the suppression of EM wave reflection from the obstacles such as buildings etc. surrounding a receiving antenna. A lot of materials for EM wave absorbers have been developed such as M-type hexagonal ferrite, $\lambda/4$ -type absorber with ITO resistive film, plastics dispersed with silicon carbide.^{3,4}

Ceramic EM wave absorbers were also developed for the use of outdoor circumstances which had fire-proof and weather-proof characteristics, but all of which operated at frequency as low as microwave frequency.^{5,6} A ceramic absorber composed of titanite, which has a relative permittivity of 35, was developed for the use of millimeter wave frequency range.

Ferroelectric ceramics have particular potential as thin electromagnetic (EM) wave absorbers due to the large relative permittivity, usually larger than 1000, and large dielectric loss

compared with ordinary ceramics. If the dielectric dispersion frequency is controlled suitably, EM wave absorbers which operate at arbitrary frequency can be realized. BaTiO₃ is one of the ferroelectric ceramics which has been tried to apply for thin EM wave absorber material.^{5,6} Because of the restraint that BaTiO₃ has dielectric dispersion is limited at around few GHz, there were some attempts to change the dispersion frequency of BaTiO₃ by adding SrO or CaO.^{7,8} However, the range was small for these additives. In this paper we report the effects of addition of light dopants such as B, Li and Na to BaTiO₃ on the dielectric dispersion with a view to enlarge the frequency shift range.

2. Experimental

A flow chart of synthesizing, forming and sintering processes for doping B, Li and Na for BaTiO₃ is shown in Fig. 1. Additives such as B₂O₃, Li₂CO₃, and C₃H₄(OH)(COONa)₃ are commercially available. A plate of BaTiO₃ doped with 0.3 mol% Li₂O was prepared. Thickness of the plate was 0.2 mm since the large permittivity is able to shorten the wavelength. A ceramic plate with thickness of 0.5 mm and relative permittivity of 21 was attached to the BaTiO₃ plate in order to suppress reflection of the incident EM wave. Complex relative permittivity was measured using three different apparatus: an impedance analyzer

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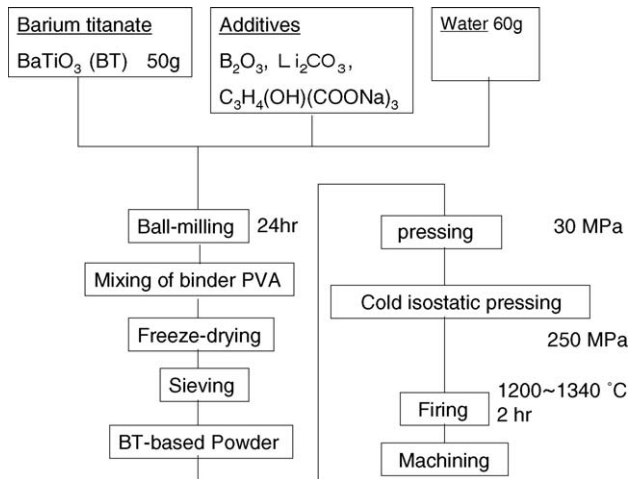


Fig. 1. Flow chart of synthesizing, forming and firing processes for BaTiO₃-based powders doped with B, Li and Na.

4194A at frequency range of 100 Hz–1 MHz, an impedance analyzer 4291B at 2 MHz–1.8 GHz, with test fixture 16192A for sub miniature device measurement, and HVS dielectric spectrometer above 33 GHz.⁹ In millimeter wave frequency, it was only possible to obtain the correct value of relative permittivity by measuring the transmission coefficient S_{21} for a very thin sample of thickness 0.2 mm. The EM wave absorption characteristic, i.e. reflectivity, was measured by free space method.⁹ XRD patterns were recorded from sintered and powdered samples to obtain crystal lattice parameters.

3. Result

Fig. 2 shows the SEM photographs of pure and BaTiO₃ added with 3 mol% Li₂O, B₂O₃ and Na₂O, which were sintered at 1270, 1250, 1200 and 1340 °C, respectively.

Complex relative permittivity ϵ' and ϵ'' of pure and Li₂O added BaTiO₃ is shown in Fig. 3 as a function of frequency. BaTiO₃ added with 3 mol% Li₂O showed a dispersion at a frequency of 0.52 MHz. In the case of 0.3 mol% Li₂O doped BaTiO₃, the dielectric dispersion was observed at around 2.5 GHz. On the other hand, addition of B₂O₃ or Na₂O did not cause such a phenomenon.

XRD curves of BaTiO₃ added with 0, 0.3, 1 and 3 mol% Li₂O are shown in Fig. 4. Pure BaTiO₃ exhibits two clear peaks of (002) and (200) planes, which correspond to ferroelectric

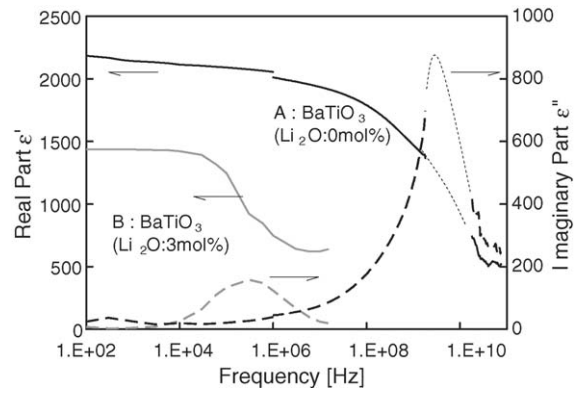


Fig. 3. Relative permittivity ϵ' and ϵ'' of pure and added BaTiO₃ with 3 mol% Li₂O as a function of frequency.

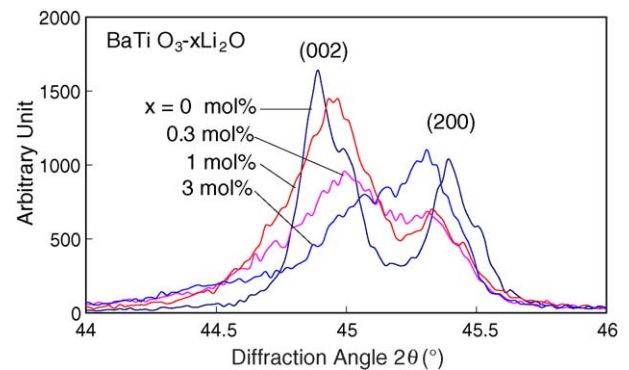


Fig. 4. XRD (002) and (200) reflection peaks of BaTiO₃ added with Li₂O.

tetragonal crystal phase. With increasing Li₂O, the two peaks approached each other and finally degenerated into a single (200) peak. The BaTiO₃ added with B₂O₃ or Na₂O has two clear peaks similar to that of pure BaTiO₃, as shown in Fig. 5.

Fig. 6 shows the temperature dependence of the relative permittivity of pure and doped BaTiO₃ with Li, B and Na. Phase transition characteristics were clearly observed for the case of B- and Na-doped BaTiO₃, and the transition temperature, T_c , shifted from that of pure BaTiO₃. On the other hand, Li-doped BaTiO₃ exhibited a weak broad peak.

Measured lattice parameters, c and a , of the doped BaTiO₃ are listed in Table 1. BaTiO₃ added with 3 mol% B₂O₃ or Na₂O has a ratio $c/a = 1.009$, which is close to the value, 1.010, for pure BaTiO₃.

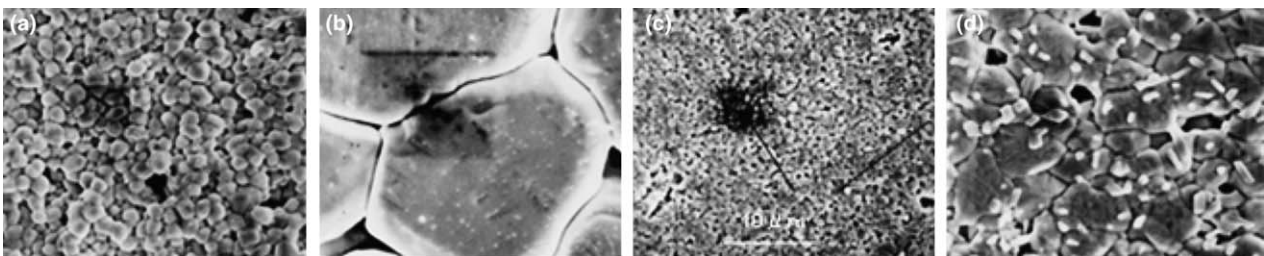


Fig. 2. SEM photographs of pure and doped BaTiO₃ with Li, B and Na. Values in the bracket show sintering temperatures: (a) pure BaTiO₃ (1270 °C); (b) Li (1250 °C); (c) B (1200 °C); (d) Na (1340 °C).

Table 1
Lattice parameters of BaTiO₃ added with Li₂O, B₂O₃ and Na₂O

Added element	Adding rate (mol%)	<i>c</i> /2 (nm)	<i>a</i> /2 (nm)	<i>c</i> / <i>a</i>	Firing temperature (°C)
Li	0	0.20186	0.1998	1.010	1270
	0.3	0.20131	0.1994	1.009	1297
	1	0.20152	0.1999	1.008	1346
	3	0.20122	0.2000	1.006	1250
B	3	0.20169	0.1998	1.009	1200
Na	3	0.20177	0.2000	1.009	1340

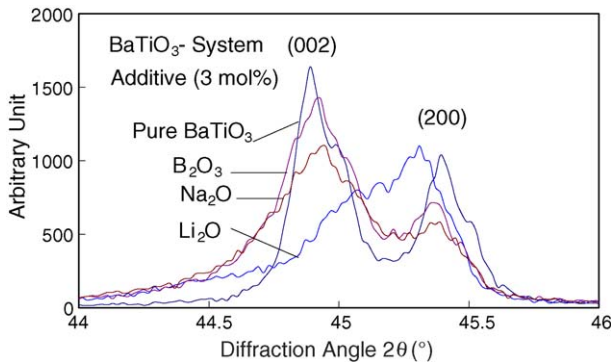


Fig. 5. XRD peaks of BaTiO₃ added with 3 mol% Li₂O, B₂O₃ and Na₂O.

It was found that the ratio *c/a* decreased with increasing Li contents. BaTiO₃ added with 0.3 mol% Li₂O was selected as an EM wave absorber for millimeter wave range.

A thin quarter wavelength EM absorber, which operates at 30 and 90 GHz could be fabricated by using 0.2 mm BaTiO₃ because the relative permittivity of BaTiO₃ is roughly 400 and the wavelength in BaTiO₃ may be shortened 1/20 as large as that in air. A plate of the BaTiO₃ system showed reflectivity as high as 97% because of the large relative permittivity beyond 2000. It was effective to reduce the reflection by using a low-loss matching dielectric layer with relative permittivity 21, which was nearly equal to the square root of that of BaTiO₃ when the minimum reflection of incident EM wave on the surface of the BaTiO₃ was occurred. The EM wave absorption characteristics of the fabricated absorber are shown in Fig. 6. The absorber showed reflectivity of −45 dB at 32 GHz and −25 dB at 95 GHz, respectively.

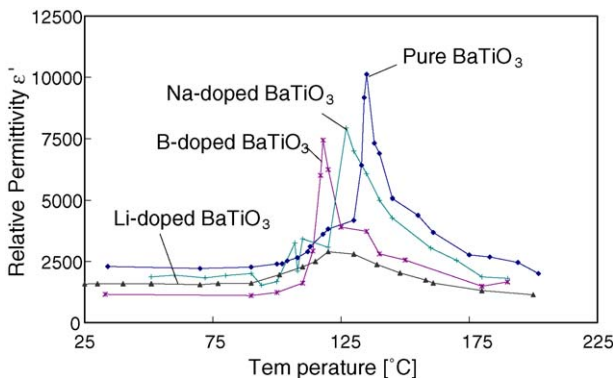


Fig. 6. Temperature dependence of relative permittivity of pure and doped BaTiO₃ with 3 mol% Li, B and Na.

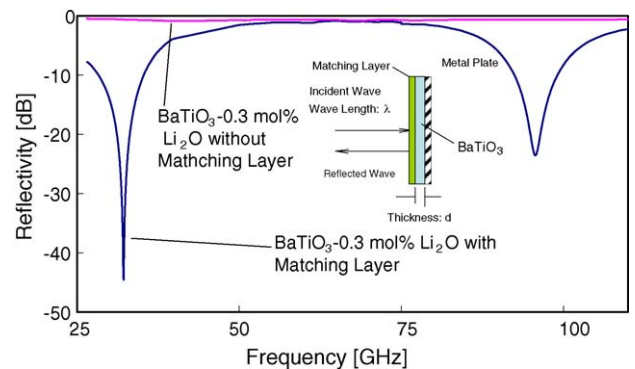


Fig. 7. EM wave absorption characteristics of BaTiO₃ added with 0.3 mol% Li₂O. Thickness of BaTiO₃ and matching layer are 0.2 and 0.5 mm, respectively.

4. Discussion

The reason why the new dielectric dispersion emerged only for Li doping is discussed below. Ionic radii of Ba²⁺, Li⁺, B³⁺, and Na⁺ ions are 0.14, 0.07, 0.02 and 0.10 nm, respectively.¹⁰ Since the radius of Li⁺ is far smaller than that of Ba²⁺, the lattice parameter changed with increasing the Li doping: the *c/a* ratio decreased and approached to 1 at 3 mol% Li accompanied with the XRD peak shift and the degeneration into a single (200) peak. The parameter change indicates that the 3 mol% Li doping brought phase transition from tetragonal ferroelectric phase to cubic paraelectric phase. Temperature dependence of relative permittivity for the Li doped BaTiO₃ in Fig. 6 also indicates that the ferroelectricity was almost lost. The new dielectric dispersion at about 0.5 MHz may be due to the piezoelectric vibration of large crystal grains of about 20 μm as shown in Fig. 2, because Li-doped BaTiO₃ had much different microstructure compared with the others.

On the other hand, the ratio *c/a* is close to that of pure BaTiO₃ ceramics for BaTiO₃ doped with 3 mol% B or Na. Ionic radius of Na⁺ resembles to that of Ba²⁺. BaTiO₃ doped with 3 mol% B or Na still has ferroelectric spontaneous polarization and dielectric dispersion similar to that of the pure BaTiO₃. The doping of Na or B caused only a shift of T_c and no new dielectric dispersion (Fig. 7).

5. Conclusion

It has been demonstrated that the dielectric dispersion frequency is decreased from several GHz to few MHz for BaTiO₃ doped with 3 mol% Li₂O. It was interpreted that the ferroelectric

phase of BaTiO₃ was disappeared by the structural phase transition from tetragonal to cubic crystal phase by the Li doping and new dielectric dispersion appeared at around 0.5 MHz. It was confirmed that the Li-doped BaTiO₃ plate attached with suitable non-reflection matching layer operated as a thin EM wave absorber at microwave and millimeter wave frequency ranges. Further investigation is necessary to clarify that excellent EM wave absorbers are realized at different frequency ranges by accurate control of Li doping.

Acknowledgements

The authors would like to thank S. Aoki, K. Nakahira and N. Kawai for cold isostatic pressing, T. Kuroyama, K. Hayakawa and D. Yokoe for machining, Y. Endou and T. Hori for measurement of dielectric properties and absorption, T. Ohta for SEM analysis, S. Suzuki for XRF analysis of BaTiO₃.

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